

The TC20 is a high voltage, high current disc pack SCR employing a high di/dt gate structure. This gate design allows the SCR to be reliably operated at high di/dt and dv/dt conditions in various phase control applications.

FEATURES:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Hermetic Ceramic Package
- Excellent Surge and I²t Ratings

APPLICATIONS:

- DC Power Supplies
- Motor Controls

ORDERING INFORMATION

Select the complete 12 digit Part Number using the table below.
 EXAMPLE: TC20442402DH is a 4400V-2450A SCR with 300ma IGT and 12 inch gate and cathode potential leads.

PART	Voltage Rating $V_{DRM}-V_{RRM}$	Voltage Code	Current Rating I_{TAVG}	Current Code	Turn-Off T_q	Gate I_{GT}	Leads
TC20	4400	44	2450	24	0	2	
	4200	42					
	4000	40			500us	300ma	12"
	3600	36			(typ.)	(max)	

Absolute Maximum Ratings

Characteristic	Symbol	Rating	Units
Repetitive Peak Voltage	$V_{DRM}-V_{RRM}$	4400	Volts
Average On-State Current, $T_C=73^{\circ}C$	$I_{T(Avg.)}$	2450	A
RMS On-State Current, $T_C=73^{\circ}C$	$I_{T(RMS)}$	3848	A
Average On-State Current, $T_C=55^{\circ}C$	$I_{T(Avg.)}$	2920	A
RMS On-State Current, $T_C=55^{\circ}C$	$I_{T(RMS)}$	4587	A
Peak One Cycle Surge Current, 60Hz, $V_R=0V$	I_{TSM}	30,000	A
Peak One Cycle Surge Current, 50Hz, $V_R=0V$	I_{TSM}	28,284	A
Fuse Coordination I^2t , 60Hz	I^2t	3.75E+06	A^2s
Fuse Coordination I^2t , 50Hz	I^2t	4.00E+06	A^2s
Critical Rate-of-Rise of On-State Current	di/dt	100	A/us
Repetitive			
Critical Rate-of-Rise of On-State Current	di/dt	300	A/us
Non-Repetitive			
Peak Gate Power, 100us	P_{GM}	16	Watts
Average Gate Power	$P_{G(avg)}$	5	Watts
Operating Temperature	T_j	-40 to+125	$^{\circ}C$
Storage Temperature	$T_{Stg.}$	-50 to+150	$^{\circ}C$
Approximate Weight		5.5	lb
		2.49	Kg
Mounting Force		12,000-15,000	lbs
		53 - 67	KNewtons

Information presented is based upon manufacturers testing and projected capabilities. This information is subject to change without notice. The manufacturer makes no claim as to suitability for use, reliability, capability or future availability of this product.

Electrical Characteristics, T_j=25°C unless otherwise specified

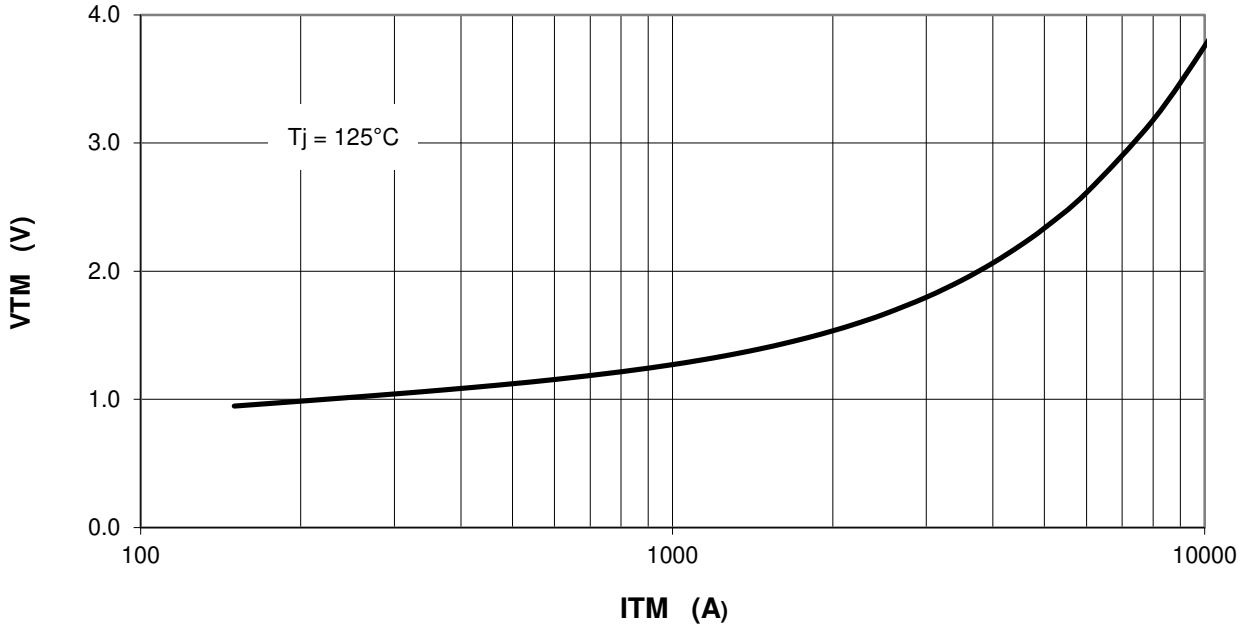
Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Repetitive Peak Forward Leakage Current	I _{DRM}	T _j =125°C, V _{DRM} =Rated			300	ma
Repetitive Peak Reverse Leakage Current	I _{RPM}	T _j =125°C, V _{RPM} =Rated			300	ma
Peak On-State Voltage	V _{TM}	T _j =125°C, I _{TM} =3000A			1.80	V
V _{TM} Model, Low Level	V ₀	T _j =125°C			0.990	V
V _{TM} = V ₀ + r•I _{TM}	r	15% I _{TM} - π•I _{TM}			2.71E-04	Ω
V _{TM} Model, High Level	V ₀	T _j =125°C			0.698	V
V _{TM} = V ₀ + r•I _{TM}	r	π•I _{TM} - I _{TSM}			3.04E-04	Ω
V _{TM} Model, 4-Term	A	T _j =125°C			0.191	
V _{TM} = A + B•Ln(I _{TM}) +	B	15% I _{TM} - I _{TSM}			0.181	
C•(I _{TM}) + D•(I _{TM}) ^{1/2}	C				3.56E-04	
	D				-1.66E-02	
Turn-On Delay Time	t _d	V _D = 0.5•V _{DRM} Gate Drive: 40V - 20Ω		1.5		us
Turn-Off Time	t _q	T _j =125°C dv/dt = 20V/us to 67% V _{DRM}			500	us
dv/dt _(Crit)	dv/dt	T _j =125°C Exp. Waveform V _D =67% Rated	1000			V/us
Gate Trigger Current	I _{GT}	T _j =25°C V _D = 12V	30	150	300	ma
Gate Trigger Voltage	V _{GT}		0.8	2.0	4.5	V
Peak Reverse Gate Voltage	V _{GRM}				5	V

Thermal Characteristics

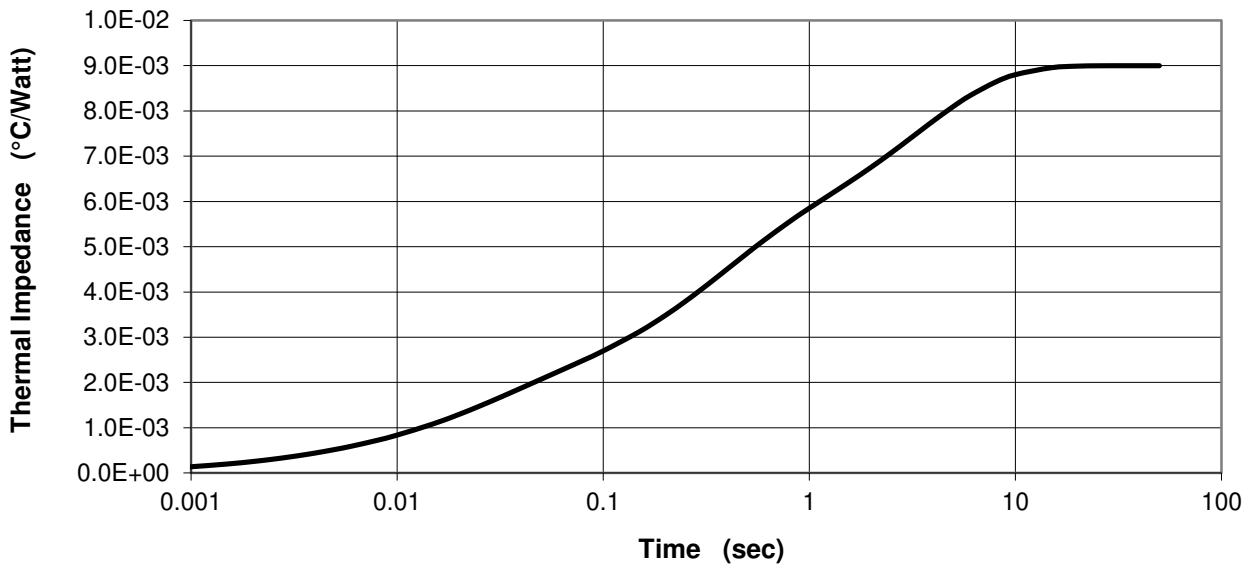
Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Thermal Resistance						
Junction to Case	Rθ _{jc}	Double side cooled			0.009	°C/Watt
Case to Sink	Rθ _{cs}	Double side cooled			0.0025	°C/Watt

Characteristic	Symbol	Test Conditions	min	typ	max	Units	
Thermal Impedance Model	Zθ _{jc}	Double side cooled					
Zθ _{jc} (t) = Σ(A(N)•(1-exp(-t/Tau(N))))		where:	N =	1	2	3	4
			A(N) =	2.00E-04	1.50E-03	3.20E-03	4.10E-03
			Tau(N) =	2.62E-03	2.31E-02	3.05E-01	3.30E+00

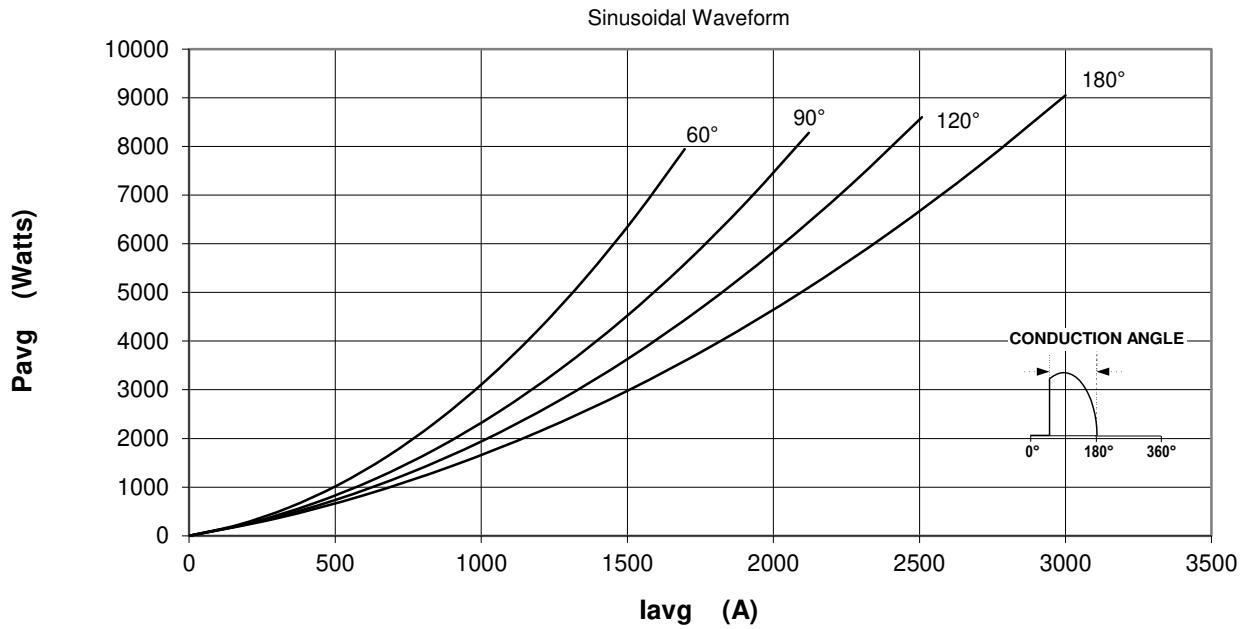
Maximum On-State Voltage Drop



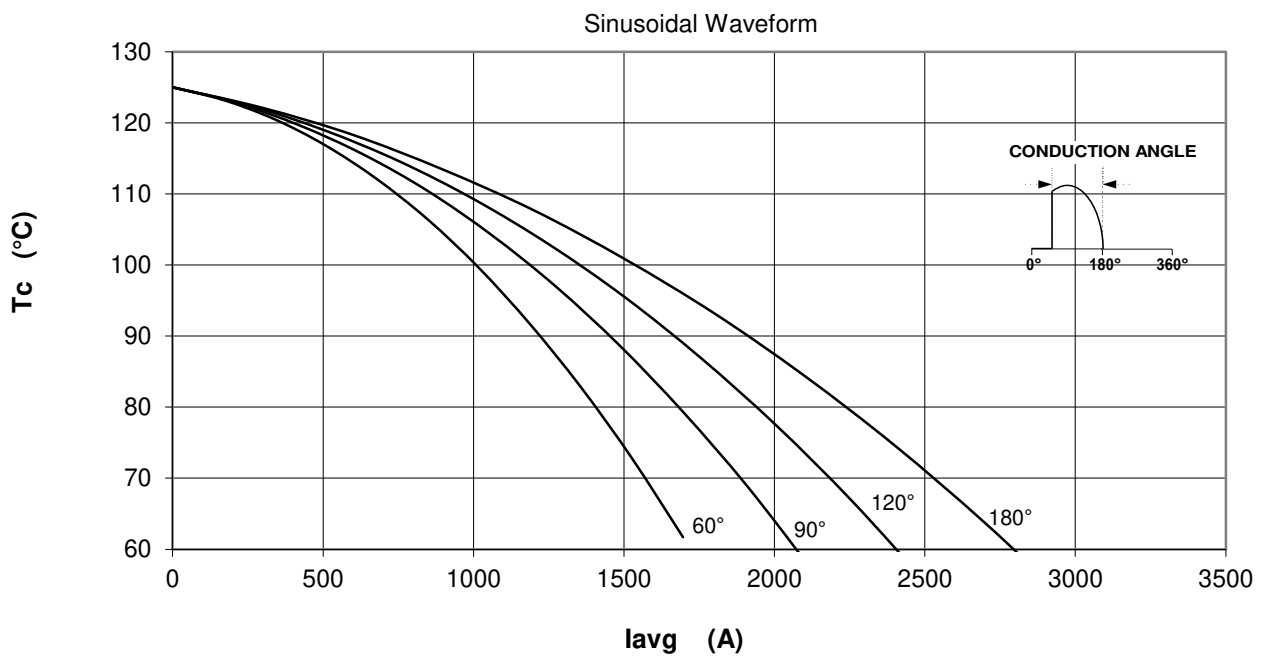
MAXIMUM TRANSIENT THERMAL IMPEDANCE



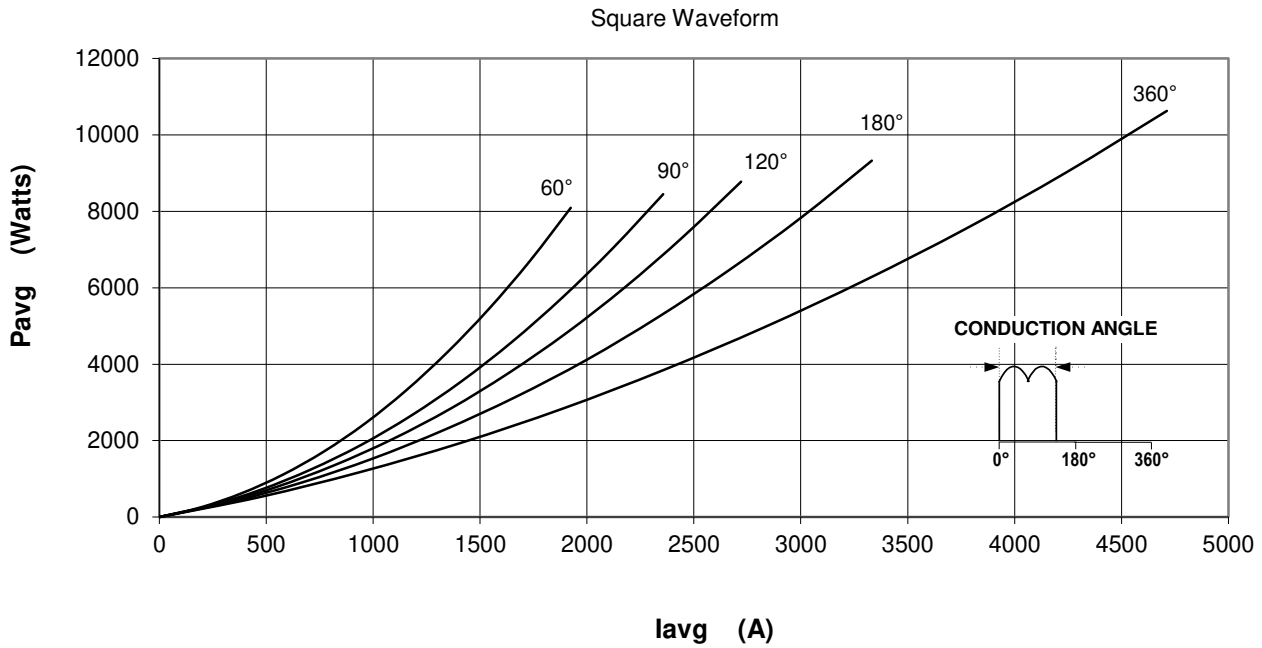
Maximum On-State Power Dissipation



Maximum Allowable Case Temperature



Maximum On-State Power Dissipation



Maximum Allowable Case Temperature

